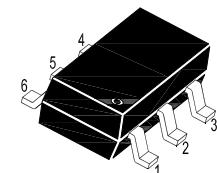
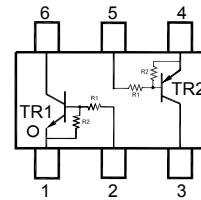


■ NPN/PNP Silicon Epitaxial Planar Digital Transistor

for switching and interface circuit and drivecircuit applications

■ Features

- Transistors with different polarity and built-in bias resistors R1(47 K Ω) and R2(47 K Ω)
- Simplification of circuit design
- Reduces number of components and board space



1. Emitter 2. Base 3. Collector
4. Emitter 5. Base 6. Collector

■ Simplified outline(SOT-363)

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

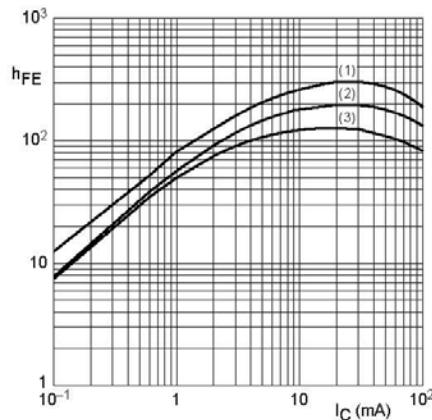
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	10	V
Input Voltage Positive Negative	V_I	+ 40 - 10	V
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	100	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Operating ambient and Storage Temperature Range	T_{stg}	- 65 to + 150	°C

■ Characteristics at $T_a = 25^\circ\text{C}$ (TR1:NPN)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5 \text{ V}$, $I_C = 5 \text{ mA}$	h_{FE}	80	-	-	-
Collector Base Cutoff Current at $V_{CB} = 50 \text{ V}$	I_{CBO}	-	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 30 \text{ V}$	I_{CEO}	-	-	1	μA
Emitter Base Cutoff Current at $V_{EB} = 5 \text{ V}$	I_{EBO}	-	-	90	μA
Collector Emitter Saturation Voltage at $I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$	$V_{CE(\text{sat})}$	-	-	0.15	V
Input Voltage (OFF) at $V_{CE} = 5 \text{ V}$, $I_C = 100 \mu\text{A}$	$V_{I(\text{OFF})}$	0.8	-	-	V
Input Voltage (ON) at $V_{CE} = 0.3 \text{ V}$, $I_C = 2 \text{ mA}$	$V_{I(\text{ON})}$	-	-	3	V
Collector Output capacitance at $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	-	2.5	pF
Input Resistance	R_1	33	47	61	K Ω
Resistance Ratio	R_1/R_2	0.8	1	1.2	-

■ Characteristics at $T_a = 25^\circ\text{C}$ (TR2:PNP)

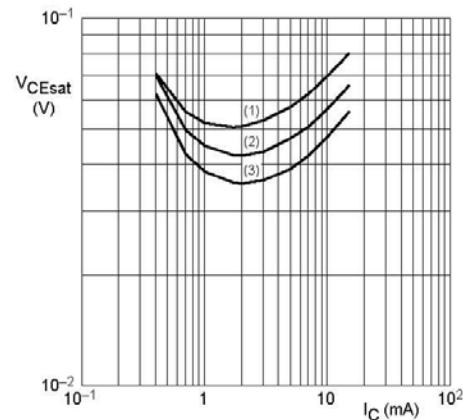
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 5 \text{ V}$, $-I_C = 5 \text{ mA}$	h_{FE}	80	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 50 \text{ V}$	$-I_{CBO}$	-	-	100	nA
Collector Emitter Cutoff Current at $-V_{CE} = 30 \text{ V}$	$-I_{CEO}$	-	-	1	μA
Emitter Base Cutoff Current at $-V_{EB} = 5 \text{ V}$	$-I_{EBO}$	-	-	90	μA
Collector Emitter Saturation Voltage at $-I_C = 10 \text{ mA}$, $-I_B = 0.5 \text{ mA}$	$-V_{CESat}$	-	-	0.15	V
Input Voltage (OFF) at $-V_{CE} = 5 \text{ V}$, $-I_C = 100 \mu\text{A}$	$-V_{I(OFF)}$	0.8	-	-	V
Input Voltage (ON) at $-V_{CE} = 0.3 \text{ V}$, $-I_C = 2 \text{ mA}$	$-V_{I(ON)}$	-	-	3	V
Collector Output capacitance at $-V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	-	3	pF
Input Resistance	R_1	33	47	61	$\text{k}\Omega$
Resistance Ratio	R_1/R_2	0.8	1	1.2	-



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = 150 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

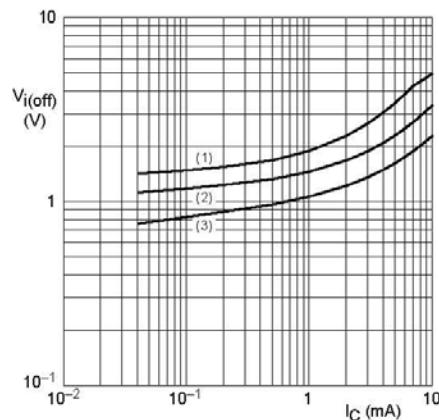
Fig. 1 DC current gain as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

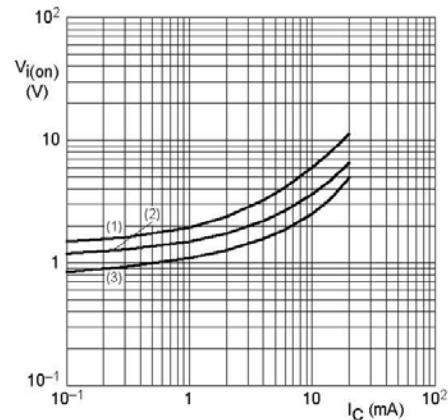
Fig. 2 Collector-emitter saturation voltage as a function of collector current; typical values.



TR1 (NPN); $V_{CE} = 5 \text{ V}$.

- (1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.

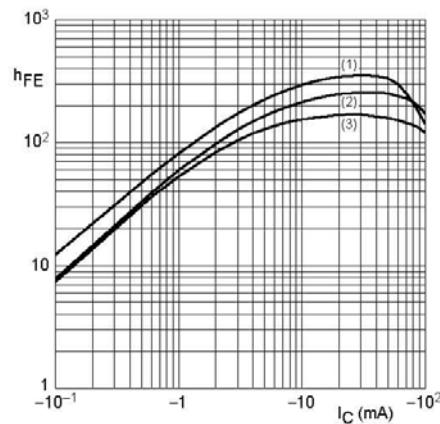
Fig. 3 Input-off voltage as a function of collector current; typical values.



TR1 (NPN); $V_{CE} = 0.3 \text{ V}$.

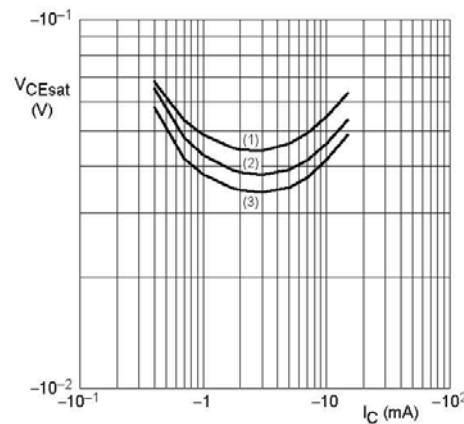
- (1) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 100 \text{ }^{\circ}\text{C}$.

Fig. 4 Input-on voltage as a function of collector current; typical values.



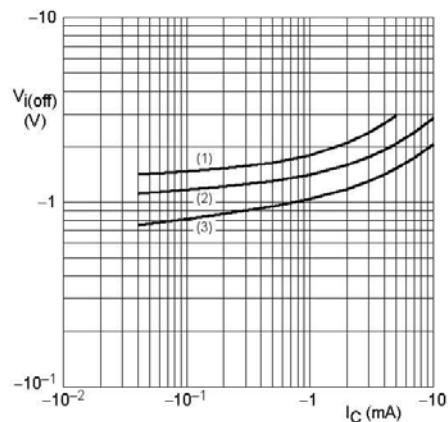
TR2 (PNP); $V_{CE} = -5$ V.
 (1) $T_{amb} = 150$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = -40$ °C.

Fig. 5 DC current gain as a function of collector current; typical values.



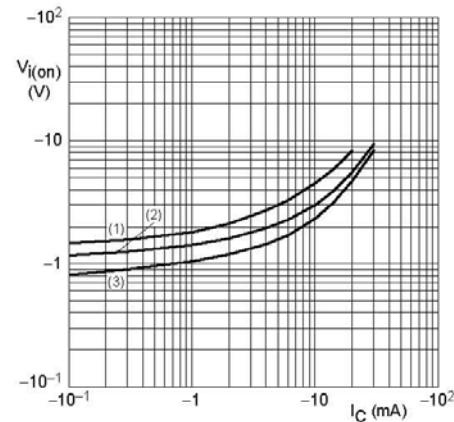
TR2 (PNP); $I_C/I_B = 20$.
 (1) $T_{amb} = 100$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = -40$ °C.

Fig. 6 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -5$ V.
 (1) $T_{amb} = -40$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = 100$ °C.

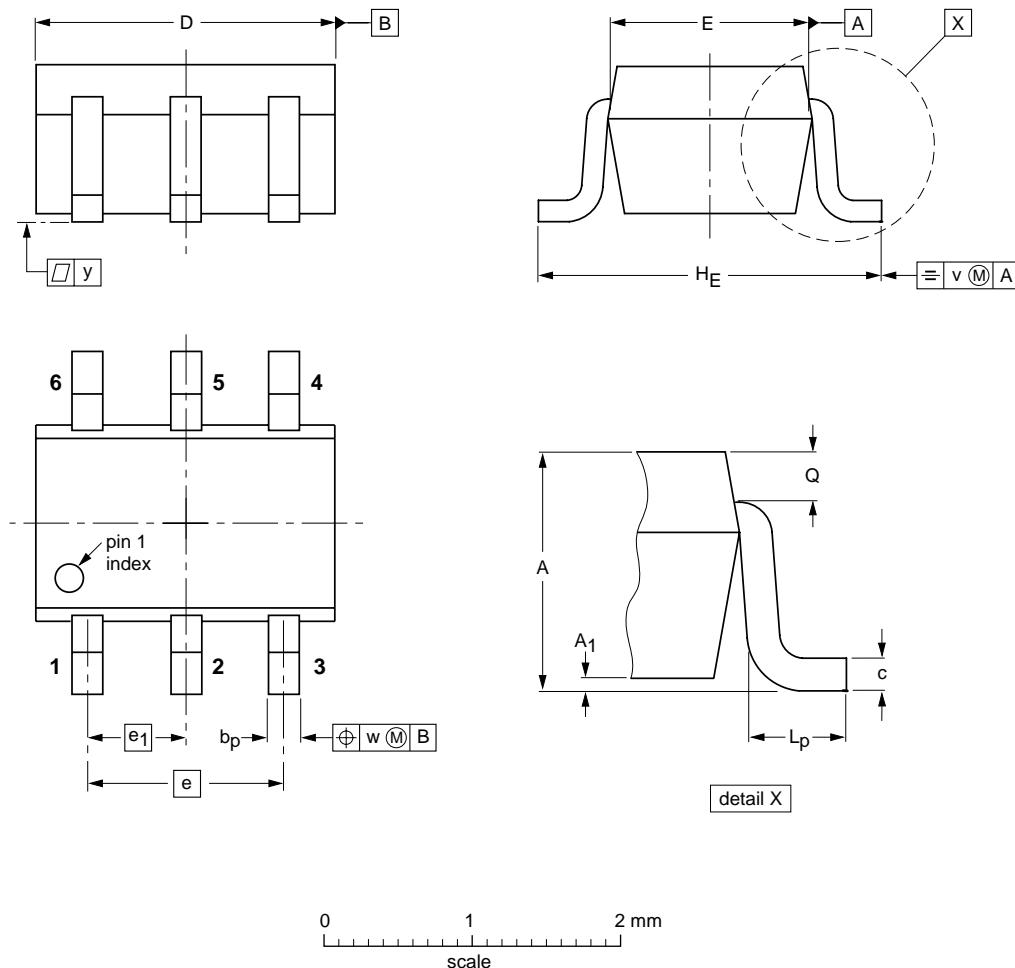
Fig. 7 Input-off voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -0.3$ V.
 (1) $T_{amb} = -40$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = 100$ °C.

Fig. 8 Input-on voltage as a function of collector current; typical values.

Package Outline SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-363	Tape/Reel, 7" reel	3000	EIA-481-1